



10Gbps 850nm GaAs PIN Photodiode Chip

Part No. PDC-85A10G

Features

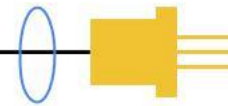
- 850nm GaAs PIN photodiode chip
- Data rate: 10Gbps
- High responsivity at 850nm
- Optimized for fiber optic application
- Low dark current and low capacitance
- Non-hermetic design



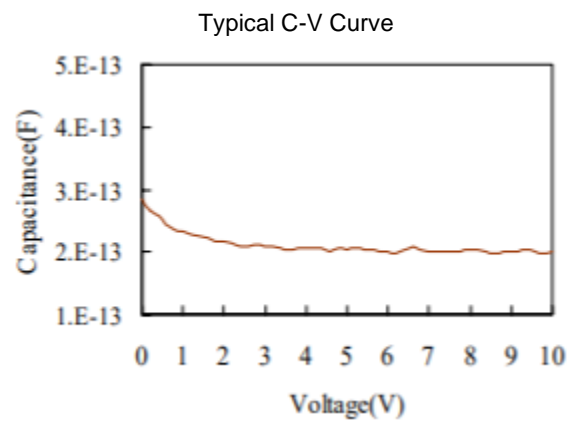
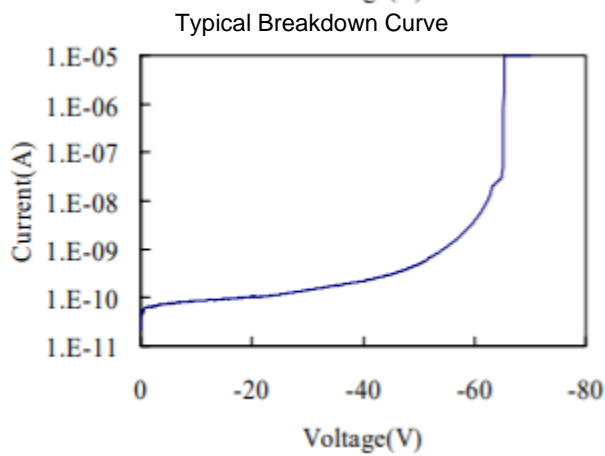
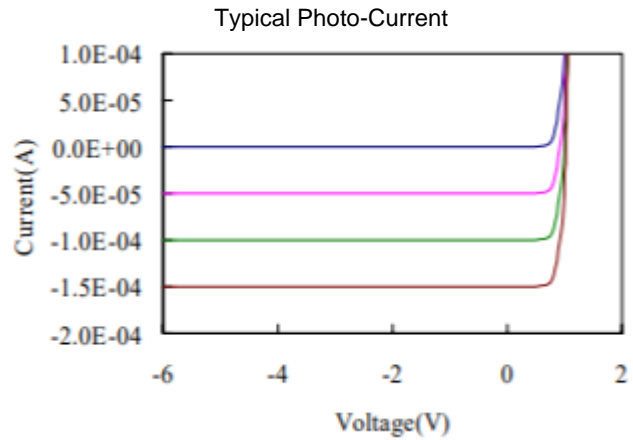
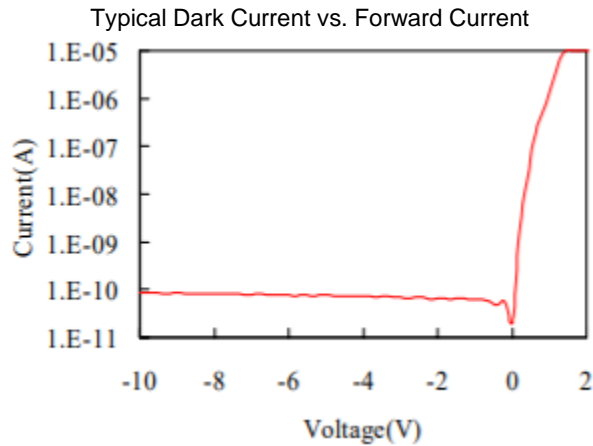
Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage temperature	-40	100	°C	
Operating temperature	-40	85	°C	
Reverse current		2	mA	T = 25°C
Forward current		10	mA	T = 25°C
Reverse voltage		20	V	T = 25°C

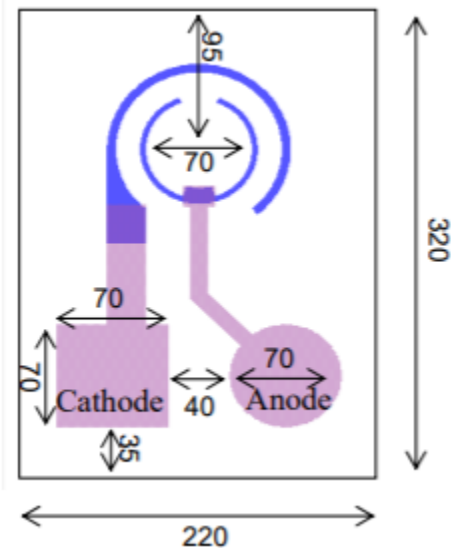
Electro-Optical Characteristics (T = 25°C)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Responsivity	R	0.55	0.65		A/W	V _R = 1.5V, λ = 850nm
Dark current	I _D		0.08	1	nA	V _R = 5V
Breakdown voltage	V _{BD}	50	65		V	I _R = 10μA
Capacitance	C		0.22	0.25	pF	V _R = 1.5V, f = 1MHz
Bandwidth	BW		9		GHz	V _R = 1.5V



Typical Characteristics



Outline Diagram



- Chip size: 220µm x 320µm typical
- Chip thickness: 200µm ±30µm
- Sensitive area: Typical 70µm in diameter

Note: Specifications are subject to change without notice.